3.3 V 16-bit transceiver; 3-state Rev. 5 — 5 April 2012

General description 1.

The 74LVTN16245B is a high-performance BiCMOS product designed for V_{CC} operation at 3.3 V.

This device is a 16-bit transceiver featuring non-inverting 3-state bus compatible outputs in both send and receive directions. The control function implementation minimizes external timing requirements. The device features an output enable input (nOE) for easy cascading and a direction input (nDIR) for direction control.

Features and benefits 2.

- 16-bit bus interface
- 3-state buffers
- Output capability: +64 mA and -32 mA
- TTL input and output switching levels
- Input and output interface capability to systems at 5 V supply
- Power-up 3-state
- Live insertion and extraction permitted
- No bus current loading when output is tied to 5 V bus
- Latch-up protection
 - JESD78B Class II exceeds 500 mA
- ESD protection:
 - HBM JESD22-A114F exceeds 2000 V
 - MM JESD22-A115-A exceeds 200 V

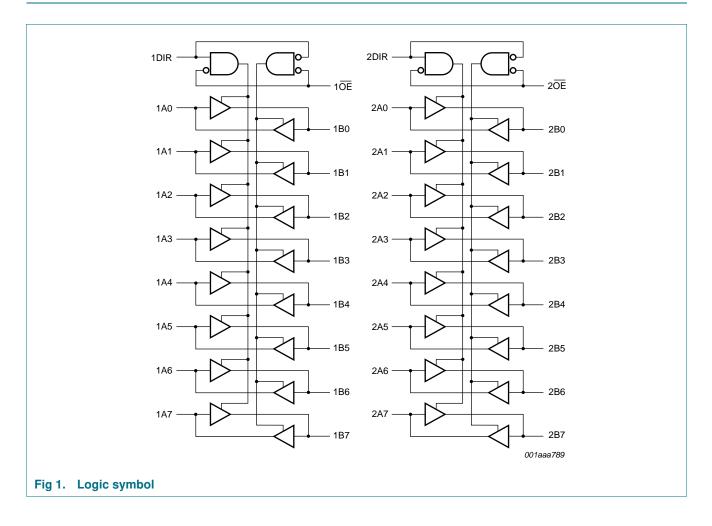
Ordering information 3.

Ordering information Table 1.

Type number	Package						
	Temperature range	Name	Description	Version			
74LVTN16245BDGG	–40 °C to +85 °C	TSSOP48	plastic thin shrink small outline package; 48 leads; body width 6.1 mm	SOT362-1			
74LVTN16245BBX	–40 °C to +125 °C	HXQFN60	plastic compatible thermal enhanced extremely thin quad flat package; no leads; 60 terminals; body $4 \times 6 \times 0.5$ mm	SOT1134-2			

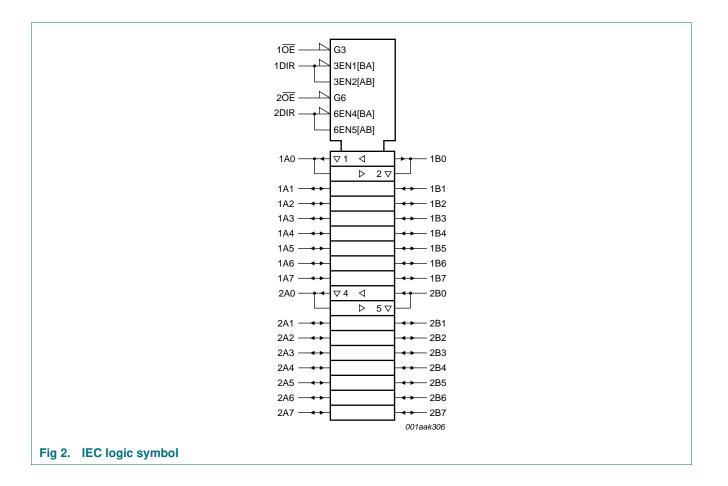


4. Functional diagram



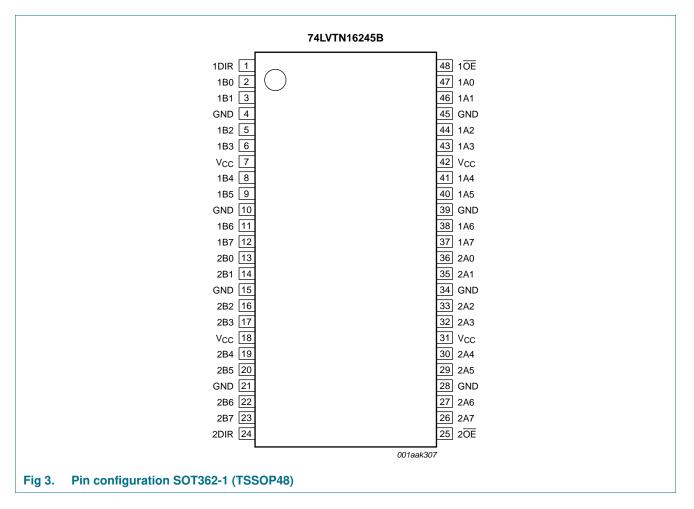
Product data sheet

3.3 V 16-bit transceiver; 3-state

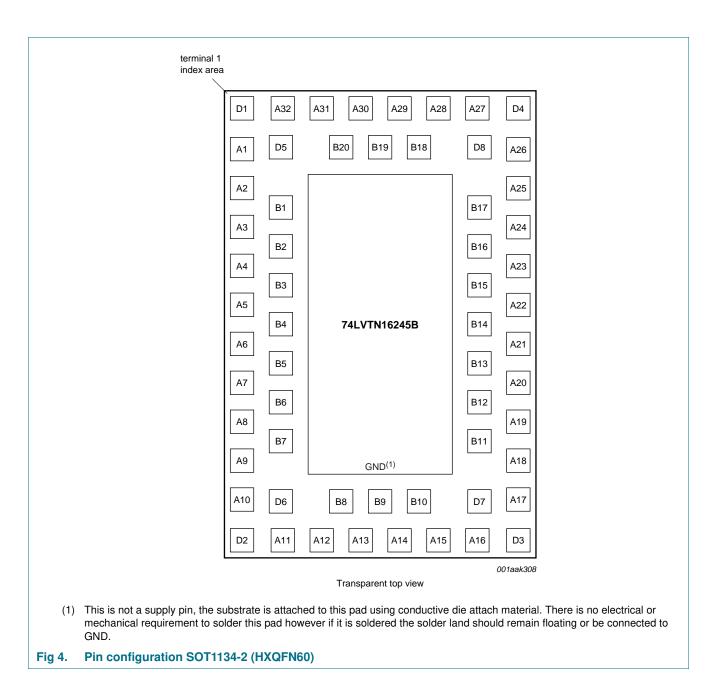


5. Pinning information

5.1 Pinning



3.3 V 16-bit transceiver; 3-state



5.2 Pin description

Symbol	Pin		Description
	SOT362-1	SOT1134-2	
1DIR, 2DIR	1, 24	A30, A13	direction control input
1B0 to 1B7	2, 3, 5, 6, 8, 9, 11, 12	B20, A31, D5, D1, A2, B2, B3, A5	data input/output
2B0 to 2B7	13, 14, 16, 17, 19, 20, 22, 23	A6, B5, B6, A9, D2, D6, A12, B8	data input/output
GND	4, 10, 15, 21, 28, 34, 39, 45	A32, A3, A8, A11, A16, A19, A24, A27	ground (0 V)
V _{CC}	7, 18, 31, 42	A1, A10, A17, A26	supply voltage
$1\overline{OE}, 2\overline{OE}$	48, 25	A29, A14	output enable input (active LOW)
2A0 to 2A7	36, 35, 33, 32, 30, 29, 27, 26	A21, B13, B12, A18, D3, D7, A15, B10	data input/output
1A0 to 1A7	47, 46, 44, 43, 41, 40, 38, 37	B18, A28, D8, D4, A25, B16, B15, A22	data input/output
n.c.	-	A4, A7, A20, A23, B1, B4, B7, B9, B11, B14, B17, B19	not connected

6. Functional description

Table 3. Function table	1]
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		Input/output		
nOE	nDIR	nAn	nBn	
L	L	output nAn = nBn	input	
L	Н	input	output nBn = nAn	
Н	Х	Z	Z	

[1] H = HIGH voltage level; L = LOW voltage level; X = don't care; Z = high-impedance OFF-state.

7. Limiting values

Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

					,
Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	+4.6	V
VI	input voltage		<u>[1]</u> –0.5	+7.0	V
Vo	output voltage	output in OFF-state or HIGH-state	<u>[1]</u> –0.5	+7.0	V
I _{IK}	input clamping current	$V_{I} < 0 V$	-50	-	mA
I _{OK}	output clamping current	$V_{O} < 0 V$	-50	-	mA
lo	output current	output in LOW-state	-	128	mA
		output in HIGH-state	-64	-	mA
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		[2] _	150	°C

Table 4. Limiting values ... continued

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
P _{tot}	total power dissipation	$T_{amb} = -40 \ ^{\circ}C \ to \ +85 \ ^{\circ}C$			
		TSSOP48 package	<u>[3]</u>	500	mW
		HXQFN60 package	<u>[4]</u> _	1000	mW

[1] The input and output negative voltage ratings may be exceeded if the input and output clamp current ratings are observed.

[2] The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability.

[3] Above 60 °C the value of P_{tot} derates linearly with 5.5 mW/K.

[4] Above 70 °C the value of P_{tot} derates linearly with 1.8 mW/K.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{CC}	supply voltage		2.7	-	3.6	V
VI	input voltage		0	-	5.5	V
V _{IH}	HIGH-level input voltage		2.0	-	-	V
V _{IL}	LOW-level input voltage		-	-	0.8	V
I _{OH}	HIGH-level output current		-32	-	-	mA
I _{OL}	LOW-level output current	none	-	-	32	mA
		$\begin{array}{l} \mbox{current duty cycle} \leq 50 \ \%; \\ f_i \geq 1 \ \mbox{kHz} \end{array}$	-	-	64	mA
T _{amb}	ambient temperature	in free-air	-40	-	+85	°C
$\Delta t / \Delta V$	input transition rise and fall rate	outputs enabled	-	-	10	ns/V

9. Static characteristics

Table 6.Static characteristics

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <mark>11</mark>	Max	Unit
T _{amb} = -4	40 °C to +85 °C					
V _{IK}	input clamping voltage	V_{CC} = 2.7 V; I_{IK} = -18 mA	-1.2	-0.85	-	V
V _{OH}	HIGH-level output voltage	I_{OH} = $-100~\mu A;$ V_{CC} = 2.7 V to 3.6 V	$V_{CC}-0.2$	V_{CC}	-	V
		$I_{OH} = -8 \text{ mA}; V_{CC} = 2.7 \text{ V}$	2.4	2.5	-	V
		$I_{OH} = -32 \text{ mA}; V_{CC} = 3.0 \text{ V}$	2.0	2.3	-	V
V _{OL}	LOW-level output voltage	$V_{CC} = 2.7 V$				
		I _{OL} = 100 μA	-	0.07	0.2	V
		$I_{OL} = 24 \text{ mA}$	-	0.3	0.5	V
		$V_{CC} = 3.0 V$				
		I _{OL} = 16 mA	-	0.25	0.4	V
		I _{OL} = 32 mA	-	0.3	0.5	V
		I _{OL} = 64 mA	-	0.4	0.55	V

Table 6. Static characteristics ... continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
I _I	input leakage current	control pins				
		V_{CC} = 3.6 V; V_{I} = V_{CC} or GND	-	0.1	±1	μA
		$V_{CC} = 0 \text{ V or } 3.6 \text{ V}; \text{ V}_{I} = 5.5 \text{ V}$	-	0.1	10	μA
		input/output data pins; V_{CC} = 3.6 V	[2]			
		V ₁ = 5.5 V	-	0.1	20	μA
		$V_{I} = V_{CC}$	-	0.5	10	μA
		$V_1 = 0 V$	-5	-0.1	-	μA
I _{OFF}	power-off leakage current	V_{CC} = 0 V; V _I or V _O = 0 V to 4.5 V	-	0.1	±100	μA
I _{LO}	output leakage current	output in HIGH-state when $V_O > V_{CC}$; $V_O = 5.5 V$; $V_{CC} = 3.0 V$	-	75	125	μA
I _{O(pu/pd)}	power-up/power-down output current	$ \begin{array}{l} V_{CC} \leq 1.2 \ V; \ V_O = 0.5 \ V \ to \ V_{CC}; \\ V_I = GND \ or \ V_{CC}; \ n\overline{OE} = don't \ care \end{array} $	[3] _	40	±100	μA
I _{CC}	supply current	V_{CC} = 3.6 V; V_{I} = GND or $V_{CC};I_{O}$ = 0 A				
		output HIGH	-	0.07	0.12	mA
		output LOW	-	4.0	6.0	mA
		outputs disabled	<u>[4]</u> _	0.07	0.12	mA
Δl _{CC}	additional supply current	per input pin; V _{CC} = 3.0 V to 3.6 V; one input at V _{CC} – 0.6 V other inputs at V _{CC} or GND	<u>[5]</u>	0.1	0.2	mA
CI	input capacitance	pins nDIR and n \overline{OE} , V _O = 0 V or 3.0 V	-	3	-	pF
C _{io(off)}	off-state input/output capacitance	pins nAn and nBn, outputs disabled; $V_O = GND$ or V_{CC}	-	9	-	pF

[1] Typical values are measured at V_{CC} = 3.3 V and at T_{amb} = 25 °C.

[2] Unused pins at V_{CC} or GND.

[3] This parameter is valid for any V_{CC} between 0 V and 1.2 V with a transition time of up to 10 ms. From V_{CC} = 1.2 V to V_{CC} = 3.3 V \pm 0.3 V a transition time of 100 μ s is permitted. This parameter is valid for T_{amb} = 25 °C only.

[4] I_{CC} is measured with outputs pulled to V_{CC} or GND.

[5] This is the increase in supply current for each input at the specified voltage level other than V_{CC} or GND.

10. Dynamic characteristics

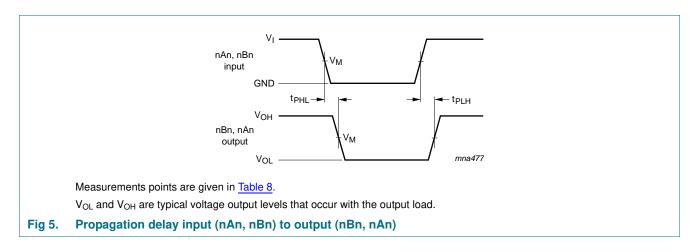
Table 7. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	Min	Typ <mark>[1]</mark>	Max	Unit
T _{amb} = -40) °C to +85 °C					
t _{PLH}	LOW to HIGH propagation delay	nAn to nBn or nBn to nAn; see <u>Figure 5</u>				
		$V_{CC} = 2.7 V$	-	-	3.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	1.9	3.3	ns
t _{PHL}	HIGH to LOW propagation delay	nAn to nBn or nBn to nAn; see <u>Figure 5</u>				
		$V_{CC} = 2.7 V$	-	-	3.5	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	1.7	3.3	ns
t _{РZH}	OFF-state to HIGH propagation delay	n <mark>OE</mark> to nAn or nBn; see <u>Figure 6</u>				
		$V_{CC} = 2.7 V$	-	-	5.3	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.8	4.5	ns
t _{PZL}	OFF-state to LOW propagation delay	n <mark>OE</mark> to nAn or nBn; see <u>Figure 6</u>				
		$V_{CC} = 2.7 V$	-	-	5.1	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.0	2.8	4.1	ns
t _{PHZ}	HIGH to OFF-state propagation delay	n <mark>OE</mark> to nAn or nBn; see <u>Figure 6</u>				
		$V_{CC} = 2.7 V$	-	-	5.7	ns
		$V_{CC} = 3.0 \text{ V} \text{ to } 3.6 \text{ V}$	1.5	3.2	5.1	ns
t _{PLZ}	LOW to OFF-state propagation delay	n <mark>OE</mark> to nAn or nBn; see <u>Figure 6</u>				
		$V_{CC} = 2.7 V$	-	-	4.6	ns
		$V_{CC} = 3.0 \text{ V}$ to 3.6 V	1.5	3.0	4.6	ns

[1] Typical values are measured at V_{CC} = 3.3 V and T_{amb} = 25 $^\circ C.$

11. Waveforms



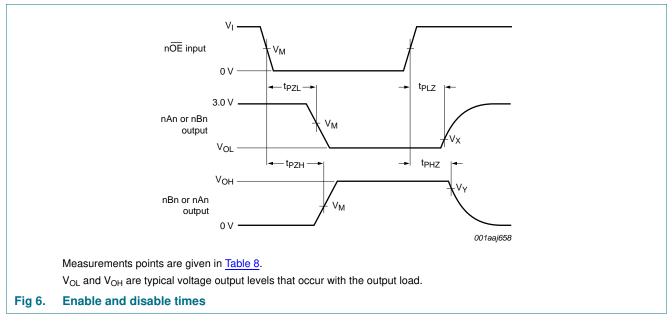


Table 8.Measurement points

Input	Output		
V _M	V _M	V _X	V _Y
1.5 V	1.5 V	V _{OL} + 0.3 V	V _{OH} – 0.3 V

3.3 V 16-bit transceiver; 3-state

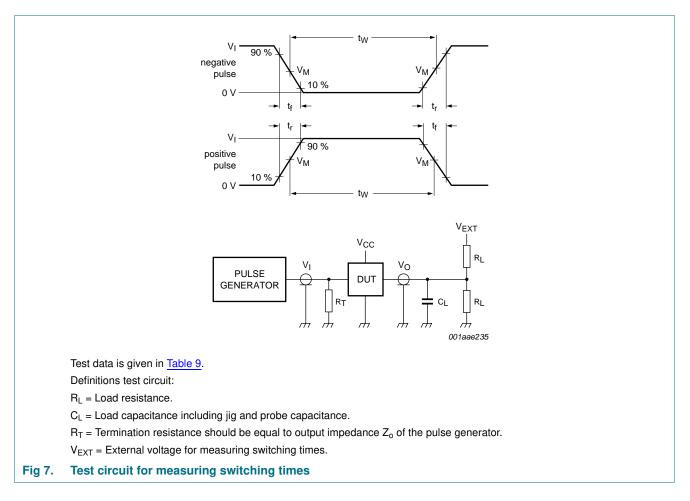


Table 9. Test data

Input			Load V _{EXT}					
VI	f _i	t _W	t _r , t _f	CL	RL	t _{PHZ} , t _{PZH}	t _{PLZ} , t _{PZL}	t _{PLH} , t _{PHL}
2.7 V	\leq 10 MHz	500 ns	\leq 2.5 ns	50 pF	500 Ω	GND	6 V	open

12. Package outline

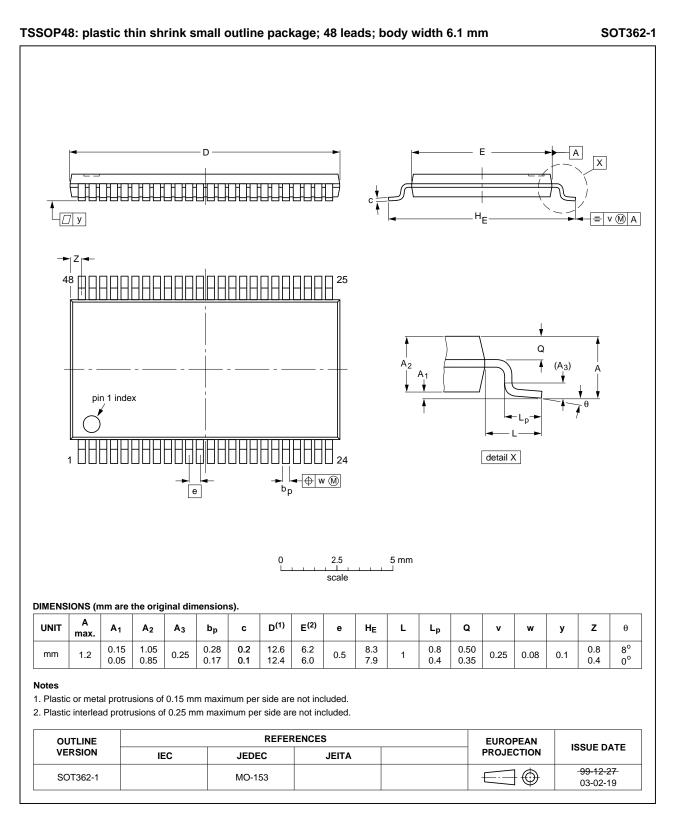
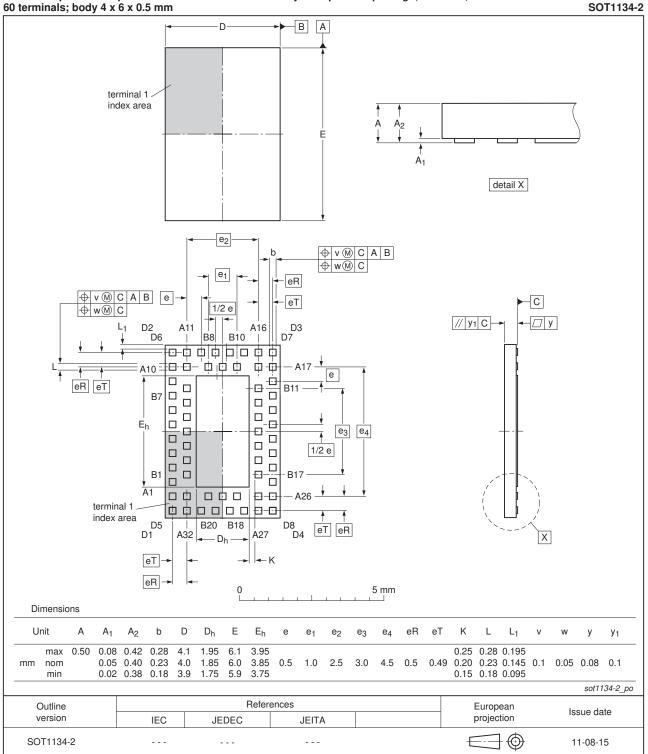


Fig 8. Package outline SOT362-1 (TSSOP48)

74LVTN16245B

74LVTN16245B 3.3 V 16-bit transceiver; 3-state



HXQFN60: plastic compatible thermal enhanced extremely thin quad flat package; no leads; 60 terminals; body 4 x 6 x 0.5 mm

Fig 9. Package outline SOT1134-2 (HXQFN60)

74LVTN16245B

13. Abbreviations

Table 10.	Abbreviations	
Acronym		Description
BiCMOS		Bipolar Complementary Metal Oxide Semiconductor
DUT		Device Under Test
ESD		ElectroStatic Discharge
HBM		Human Body Model
MM		Machine Model
TTL		Transistor-Transistor Logic

14. Revision history

Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74LVTN16245B v.5	20120405	Product data sheet	-	74LVTN16245B v.4
Modifications:	 For type nur 	nber 74LVTN16245BBX the SC	OT code has change	d to SOT1134-2
74LVTN16245B v.4	20111122	Product data sheet	-	74LVTN16245B v.3
Modifications:	 Legal pages 	updated.		
74LVTN16245B v.3	20110615	Product data sheet	-	74LVTN16245B v.2
74LVTN16245B v.2	20100323	Product data sheet	-	74LVTN16245B v.1
74LVTN16245B v.1	20090729	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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